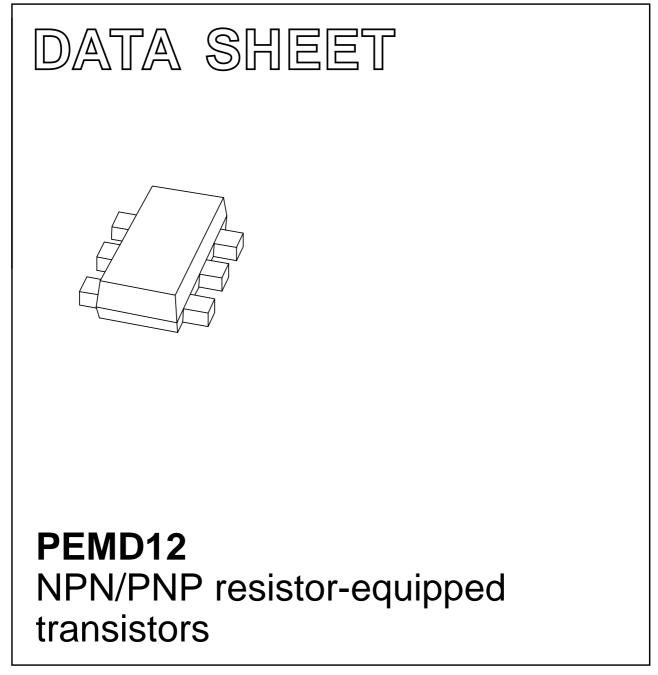
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 2001 Aug 30

2001 Nov 07



PEMD12

FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm x 1.2 mm ultra thin package
- Excellent coplanarity due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

DESCRIPTION

NPN/PNP resistor-equipped transistor in a SOT666 plastic package.

MARKING

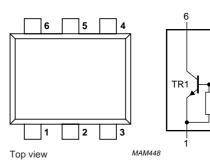
TYPE NUMBER	MARKING CODE		
PEMD12	D2		

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	50	V
I _{CM}	peak collector current	100	mA
R1	bias resistor	47	kΩ
R2	bias resistor	47	kΩ

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



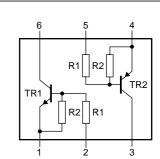


Fig.1 Simplified outline (SOT666) and symbol.

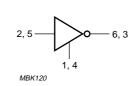


Fig.2 Equivalent inverter symbol.

PEMD12

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor for the PNP transistor with negative polarity					
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
VI	input voltage TR1				
	positive		_	+40	V
	negative		_	-10	V
	input voltage TR2				
	positive		_	+10	V
	negative		_	-40	V
lo	output current (DC)		-	100	mA
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; notes 1 and 2	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device			ŀ		
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C;$ note 1	_	300	mW

Notes

1. Transistor mounted on an FR4 printed-circuit board.

2. The only recommended soldering is reflow soldering.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W	

Notes

1. Transistor mounted on an FR4 printed-circuit board.

2. The only recommended soldering is reflow soldering.

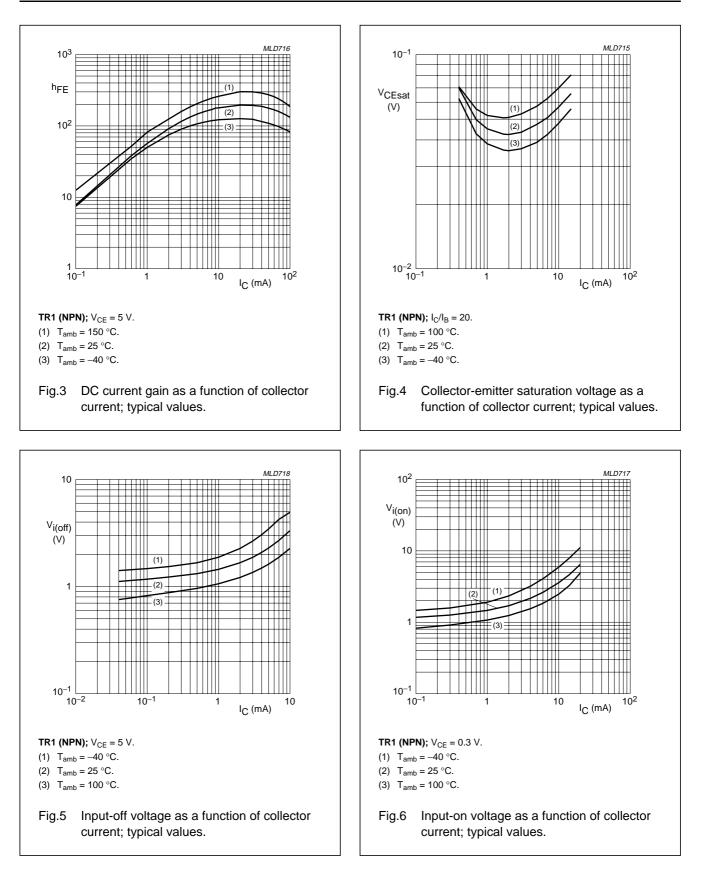
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CHARACTERISTICS

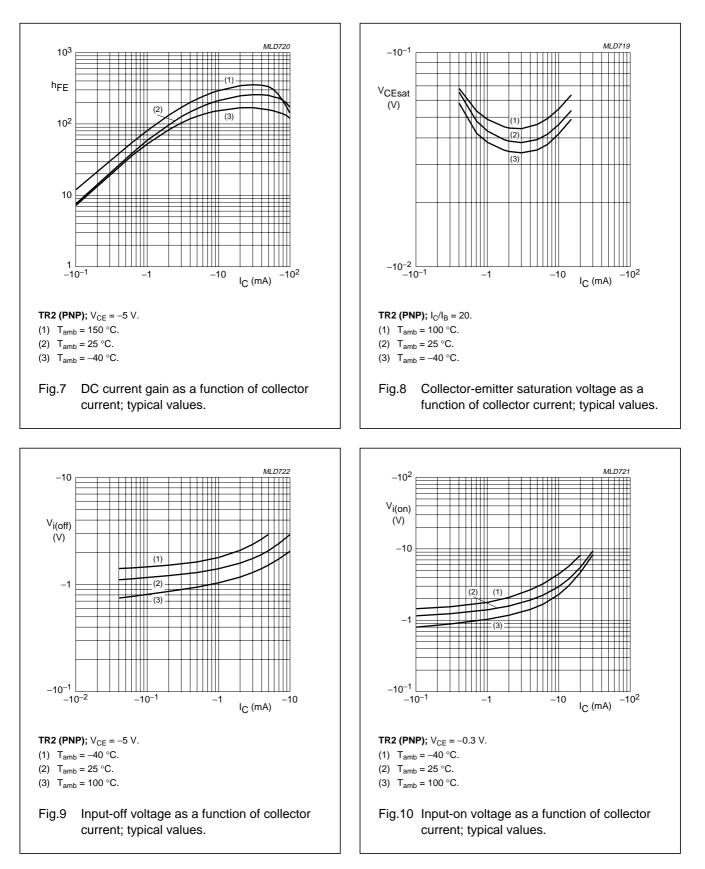
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transist	Per transistor for the PNP transistor with negative polarity					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; \text{ I}_{B} = 0$	-	-	1	μA
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	-	-	90	μA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	-	_	
V _{CEsat}	saturation voltage	$I_{\rm C} = 10 \text{ mA}; I_{\rm B} = 0.5 \text{ mA}$	-	-	150	mV
V _{i(off)}	input off voltage	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 100 \mu\text{A}$	-	1.2	0.8	V
V _{i(on)}	input on voltage	$V_{CE} = 0.3 \text{ V}; I_C = 2 \text{ mA}$	3	1.6	_	V
R ₁	input resistor		33	47	61	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_{E} = i_{e} = 0; V_{CB} = 10 V;$				
	TR1 (NPN)	f = 1 MHz	-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

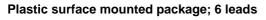
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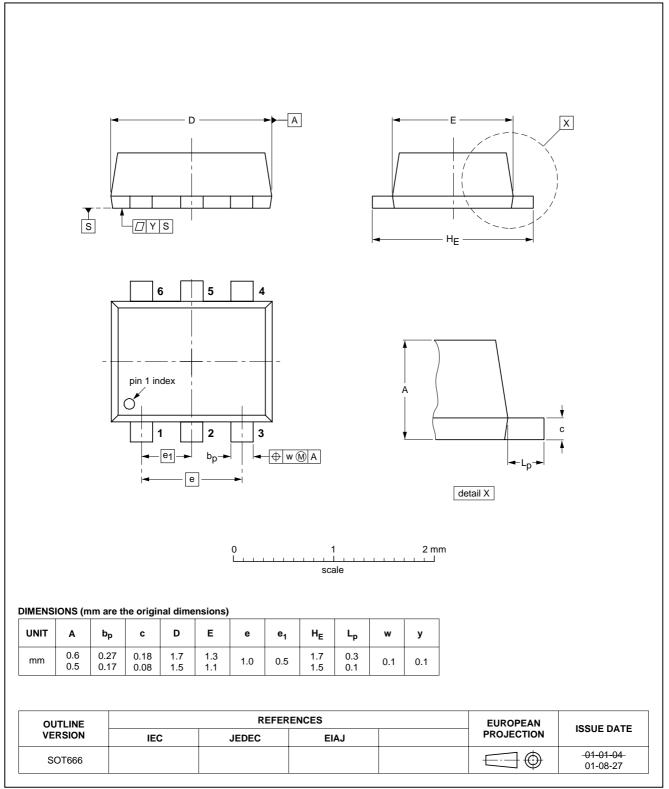


PEMD12



PACKAGE OUTLINE





PEMD12

SOT666

PEMD12

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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PEMD12

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